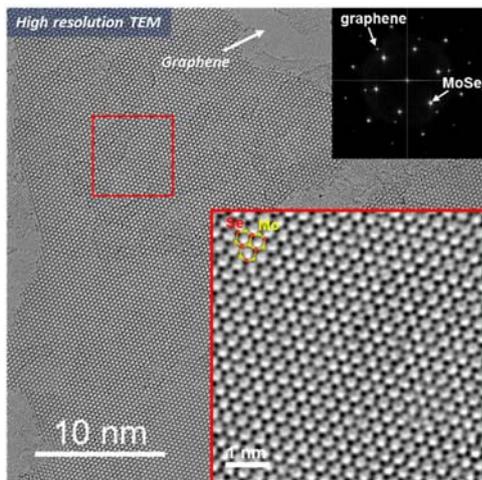


05: Growth by van der Waals epitaxy and characterization of two-dimensional transition metal diselenides

Frédéric BONELL, Matthieu JAMET, Alain MARTY and Céline VERGNAUD
IRIG-Spintec, Université Grenoble-Alpes, CEA, CNRS and Grenoble INP

Layer-structured transition metal dichalcogenides (TMDs) have drawn much attention recently since they are being considered as a new class of semiconducting two-dimensional (2D) materials with thickness-tunable band-gap modulation. In the single-layer configuration, the TMDs offer a unique platform to explore not only the carrier transport in an ultrathin



channel but also the control of 2D excitonic systems and the spin-valley physics. Molecular beam epitaxy (MBE) is of particular interest to grow such materials because one can obtain high purity layers with a precise control of the thickness and a flexible choice of metals. Most importantly, MBE allows for the growth of TMDs over large areas (cm^2) which is the blocking point for the use of such materials at the industrial level nowadays.

In our lab, we have developed the van der Waals epitaxy of TMDs by co-depositing in ultrahigh vacuum the transition metal (Mo, W, Sn, Pt...) and the selenium. The example of a single MoSe_2 layer grown on CVD graphene is shown in the figure. In the van der Waals epitaxy process, the interaction between the substrate and the epilayer is so weak (of van der Waals type) that the TMDs grow directly with their bulk characteristics even at the single layer level. By this, we can grow high quality single-crystalline layers over large areas.

In this training course, we propose the attendees to grow MoSe_2 multilayers by van der Waals epitaxy on mica or graphene. For this purpose, they will use a molecular beam epitaxy machine equipped with Reflection High Energy Electron Diffraction to monitor *in-situ* the structure and morphology of the film. The TMD film will be first characterized by Raman spectroscopy to verify the crystalline quality through the observation of the vibration modes. Then, high resolution x-ray diffraction in grazing incidence will be performed to study the crystalline quality of the TMD layers.

References

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